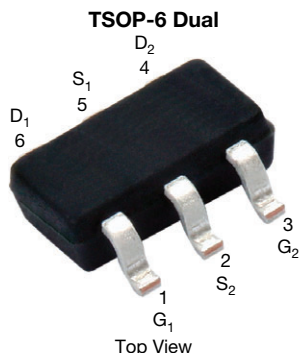


## N- and P-Channel 30 V (D-S) MOSFET

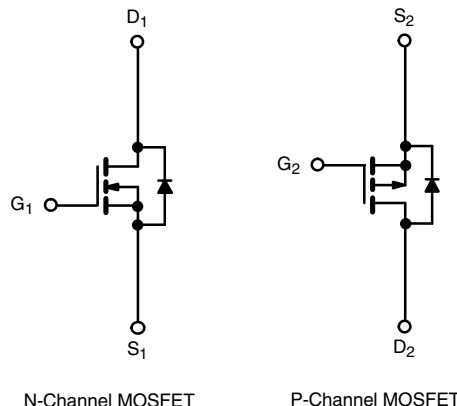


### FEATURES

- TrenchFET® power MOSFET
- 100 %  $R_g$  tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



PRODUCT SUMMARY		
	N-CHANNEL	P-CHANNEL
$V_{DS}$ (V)	30	-30
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = \pm 10$ V	0.105	0.200
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = \pm 4.5$ V	0.175	0.360
$Q_g$ typ. (nC)	2.1	2.4
$I_D$ (A) <sup>a</sup>	2.5	-1.8
Configuration	N- and p-pair	

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free	Si3552DV-T1-E3
Lead (Pb)-free and halogen-free	Si3552DV-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-source voltage		V <sub>DS</sub>	30	-30	V
Gate-source voltage		V <sub>GS</sub>	± 20	± 20	
Continuous drain current (T <sub>J</sub> = 150 °C) a, b	T <sub>A</sub> = 25 °C	I <sub>D</sub>	2.5	-1.8	A
	T <sub>A</sub> = 70 °C		2	-1.2	
Pulsed drain current		I <sub>DM</sub>	8	-7	
Continuous source current (diode conduction) a, b		I <sub>S</sub>	1.05	-1.05	
maximum power dissipation a, b	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.15		W
	T <sub>A</sub> = 70 °C		0.73		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient <sup>a</sup>	$R_{thJA}$	93	110	$^\circ\text{C/W}$	
		130	150		
Maximum junction-to-lead	$R_{thJL}$	75	90		

### Notes

- a. Surface mounted on FR4 board  
b.  $t \leq 5$  s



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	N-Ch	1	-	-	V
		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	P-Ch	-1	-	-	
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	N-Ch	-	-	± 100	nA
			P-Ch	-	-	± 100	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	N-Ch	-	-	1	μA
		V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V	P-Ch	-	-	-1	
		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	N-Ch	-	-	5	
		V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	P-Ch	-	-	-5	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	N-Ch	5	-	-	A
		V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -10 V	P-Ch	-5	-	-	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A	N-Ch	-	0.085	0.105	Ω
		V <sub>GS</sub> = -10 V, I <sub>D</sub> = -1.8 A	P-Ch	-	0.165	0.200	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 2 A	N-Ch	-	0.140	0.175	
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1.2 A	P-Ch	-	0.298	0.360	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.5 A	N-Ch	-	4.3	-	S
		V <sub>DS</sub> = -15 V, I <sub>D</sub> = -1.8 A	P-Ch	-	2.4	-	
Diode forward voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 1.05 A, V <sub>GS</sub> = 0 V	N-Ch	-	0.81	1.1	V
		I <sub>S</sub> = -1.05 A, V <sub>GS</sub> = 0 V	P-Ch	-	-0.83	-1.1	
Dynamic <sup>b</sup>							
Total gate charge	Q <sub>g</sub>	N-Channel V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 1.8 A  P-Channel V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -5 V, I <sub>D</sub> = -1.8 A	N-Ch	-	2.1	3.2	nC
Gate-source charge	Q <sub>gs</sub>		P-Ch	-	2.4	3.6	
			N-Ch	-	0.7	-	
Gate-drain charge	Q <sub>gd</sub>		P-Ch	-	0.9	-	
			N-Ch	-	0.7	-	
			P-Ch	-	0.8	-	
Gate resistance	R <sub>g</sub>	N-Channel V <sub>DD</sub> = 15 V, R <sub>L</sub> = 15 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 Ω  P-Channel V <sub>DD</sub> = -15 V, R <sub>L</sub> = 15 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 6 Ω	N-Ch	0.5	-	2.4	Ω
			P-Ch	3	-	11	
Turn-on delay time	t <sub>d(on)</sub>		N-Ch	-	7	11	ns
			P-Ch	-	8	12	
Rise time	t <sub>r</sub>		N-Ch	-	9	14	
			P-Ch	-	12	18	
Turn-off delay time	t <sub>d(off)</sub>		N-Ch	-	13	20	
			P-Ch	-	12	18	
Fall time	t <sub>f</sub>		N-Ch	-	5	8	
			P-Ch	-	7	11	
Source-drain reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 1.05 A, di/dt = 100 A/μs	N-Ch	-	35	60	
		I <sub>F</sub> = -1.05 A, di/dt = 100 A/μs	P-Ch	-	30	60	

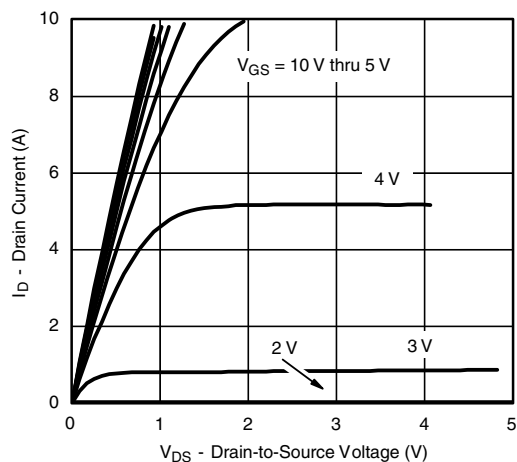
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

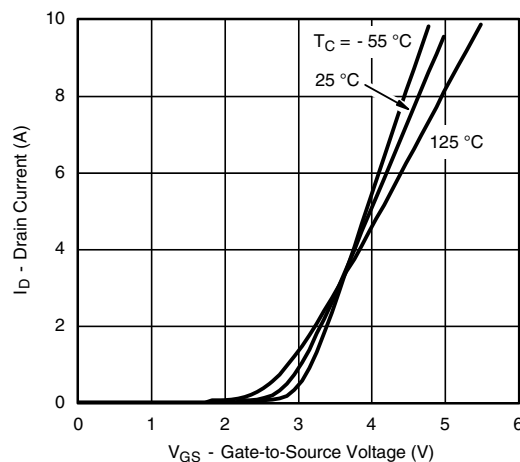
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



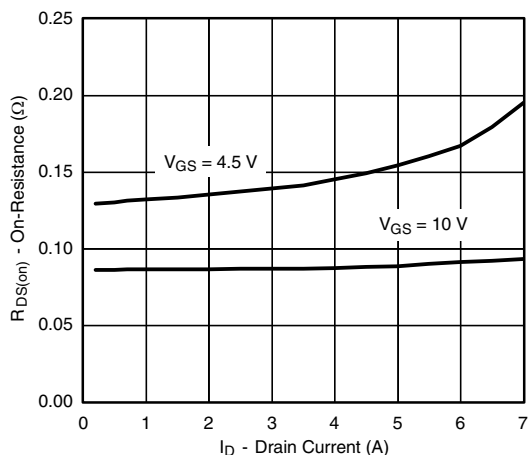
**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



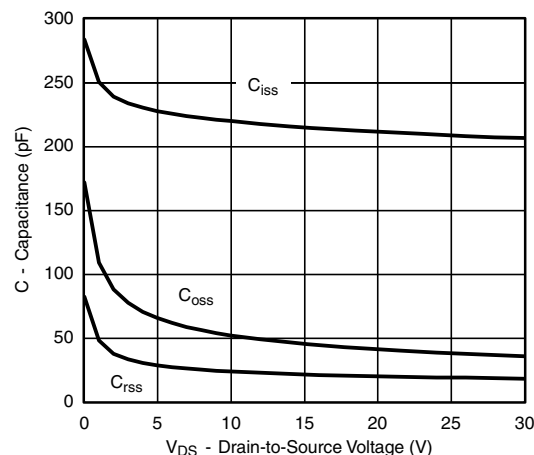
**Output Characteristics**



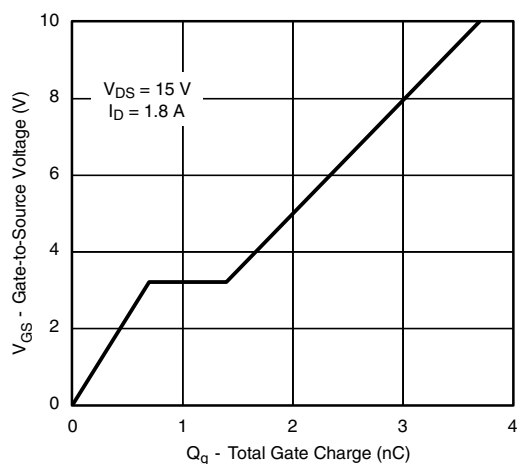
**Transfer Characteristics**



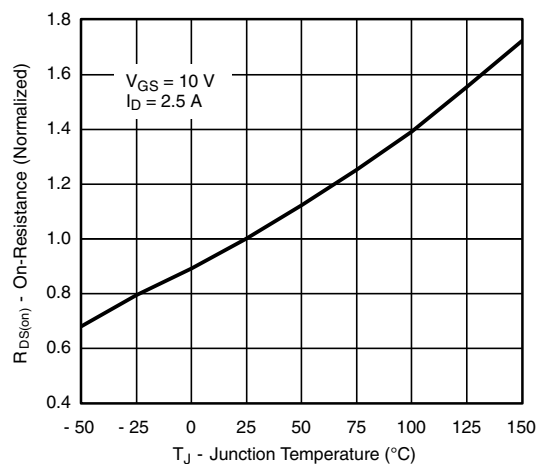
**On-Resistance vs. Drain Current**



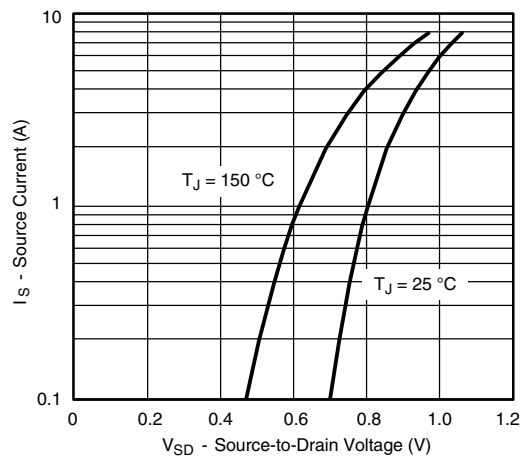
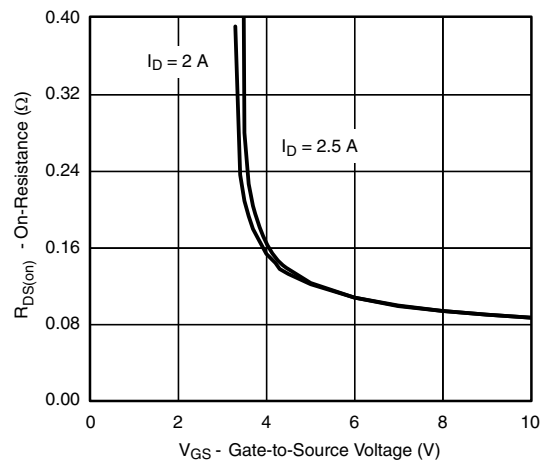
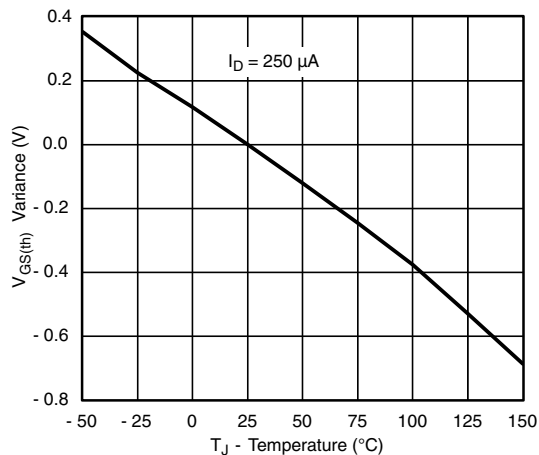
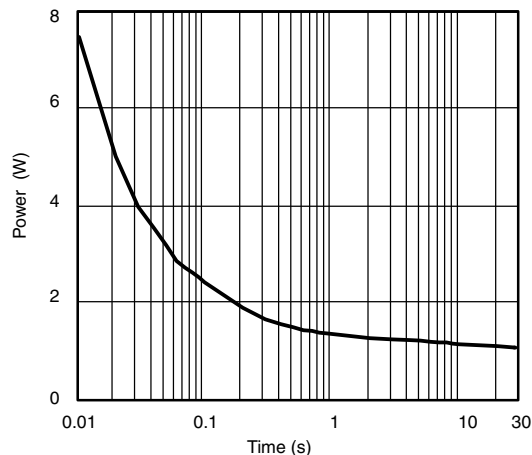
**Capacitance**



**Gate Charge**

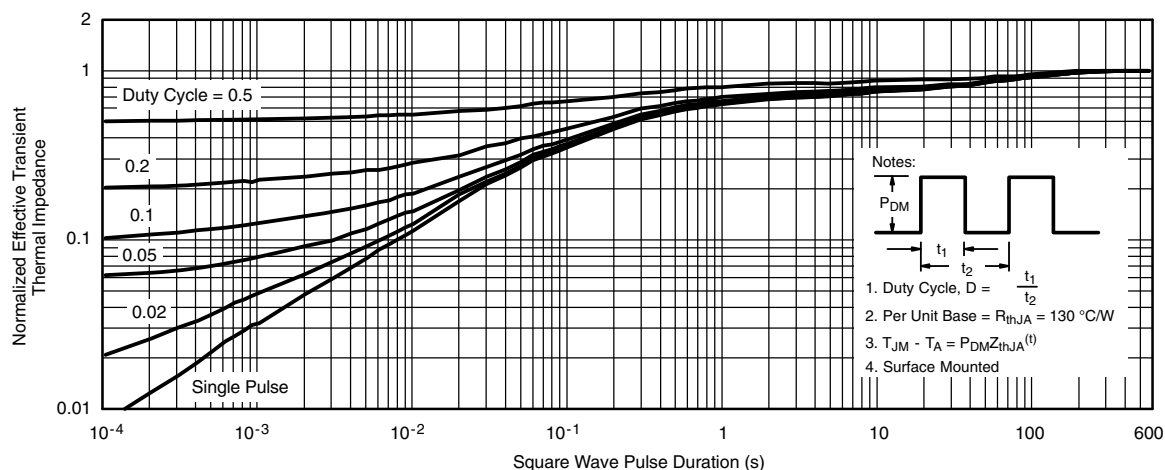


**On-Resistance vs. Junction Temperature**

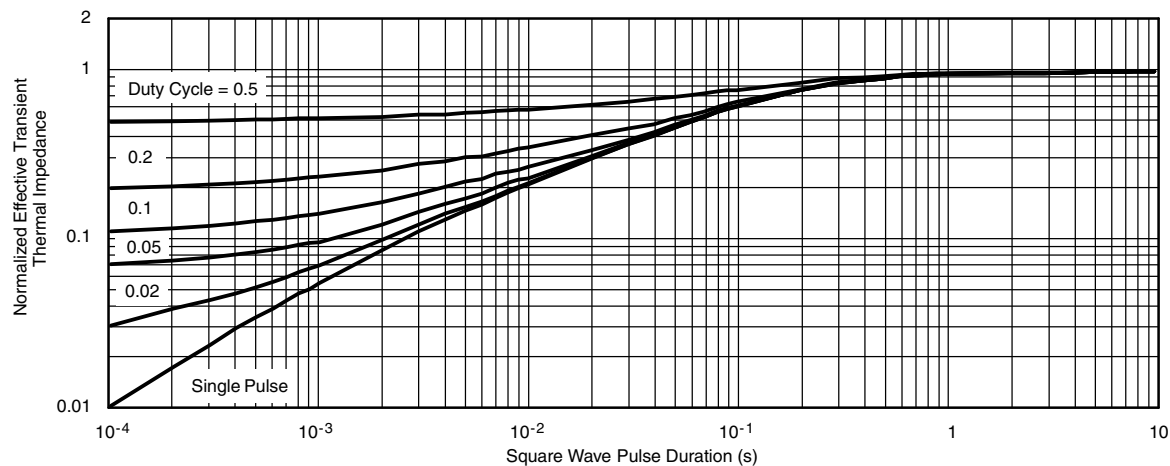
**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Source-Drain Diode Forward Voltage**

**On-Resistance vs. Gate-to-Source Voltage**

**Threshold Voltage**

**Single Pulse Power (Junction-to-Ambient)**



**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



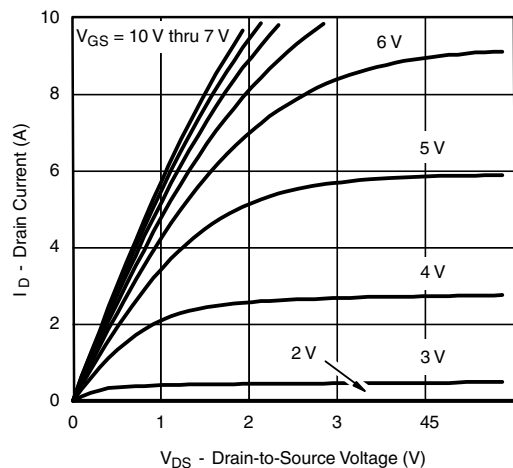
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



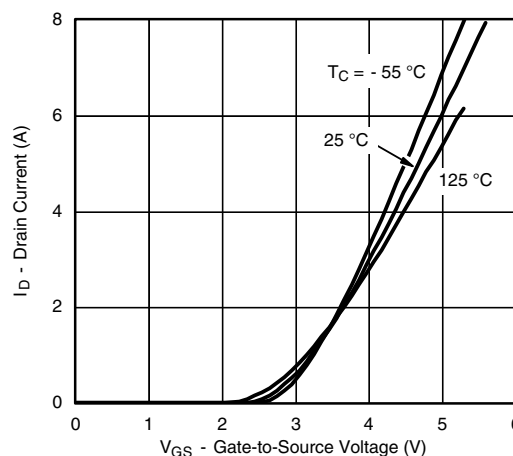
**Normalized Thermal Transient Impedance, Junction-to-Foot**



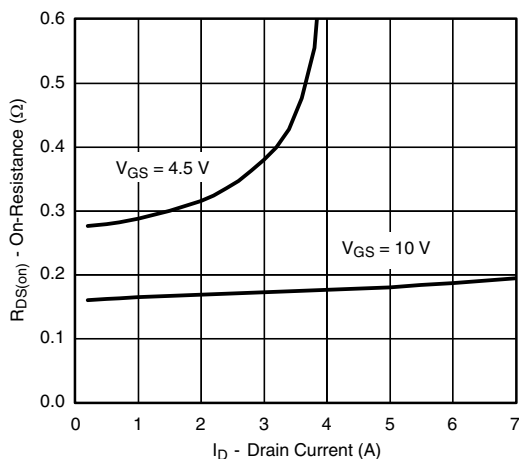
**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



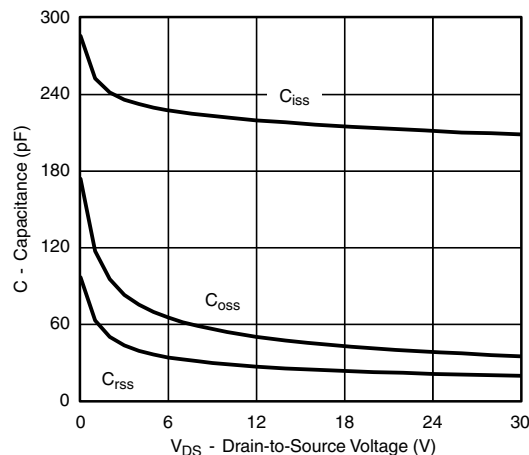
**Output Characteristics**



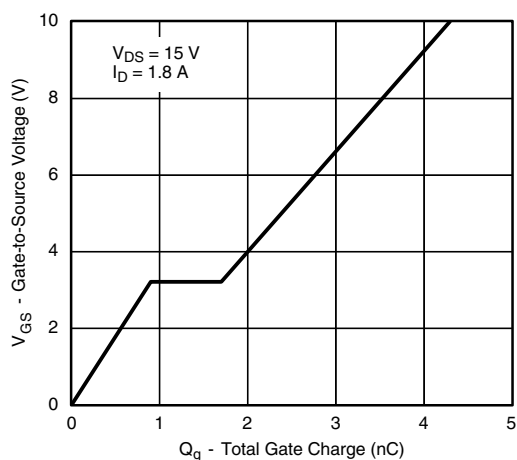
**Transfer Characteristics**



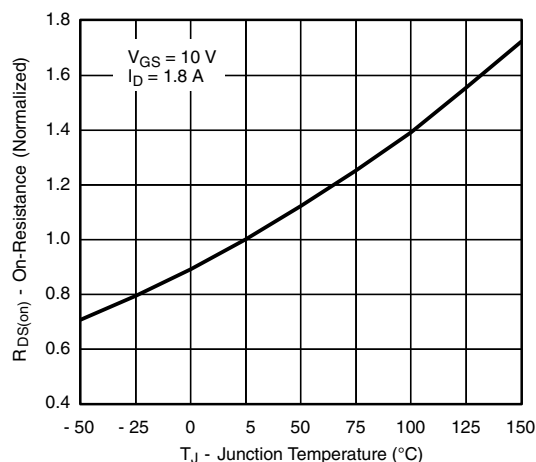
**On-Resistance vs. Drain Current**



**Capacitance**



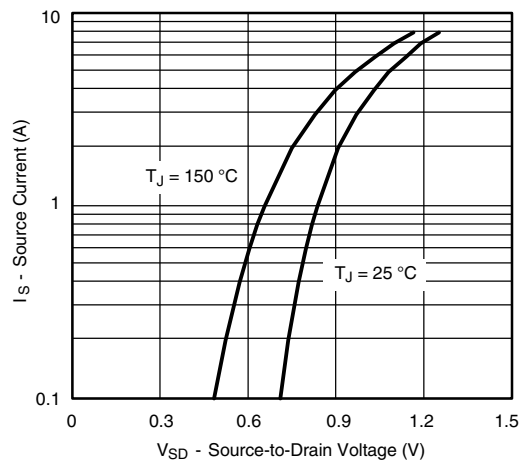
**Gate Charge**



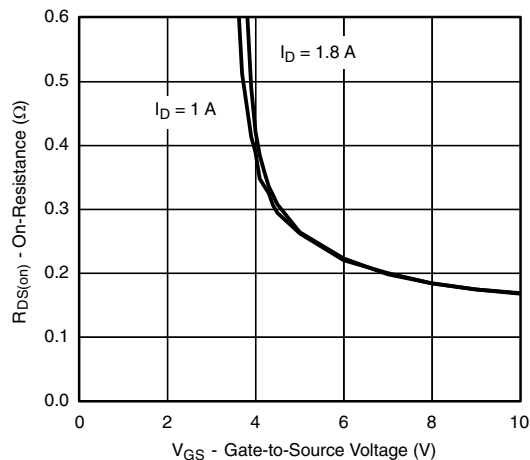
**On-Resistance vs. Junction Temperature**



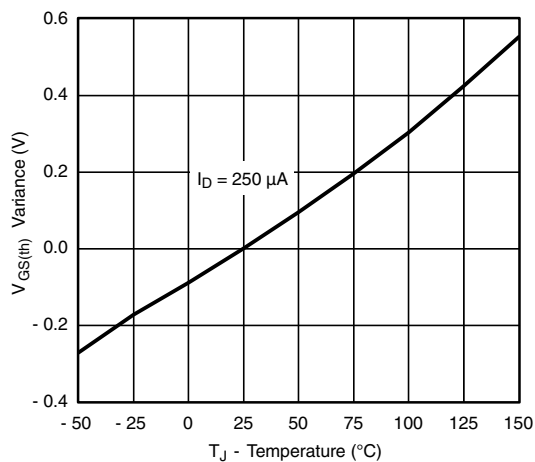
**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



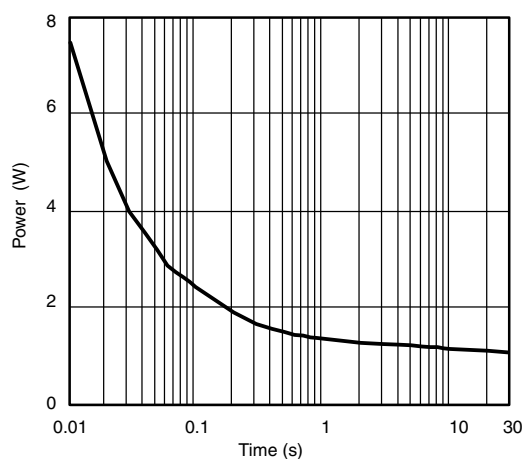
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



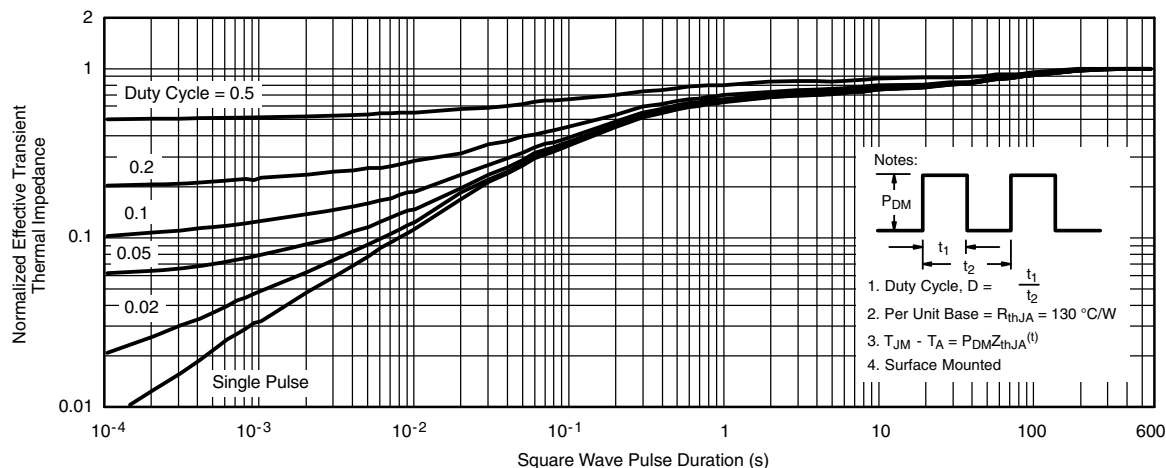
**Threshold Voltage**



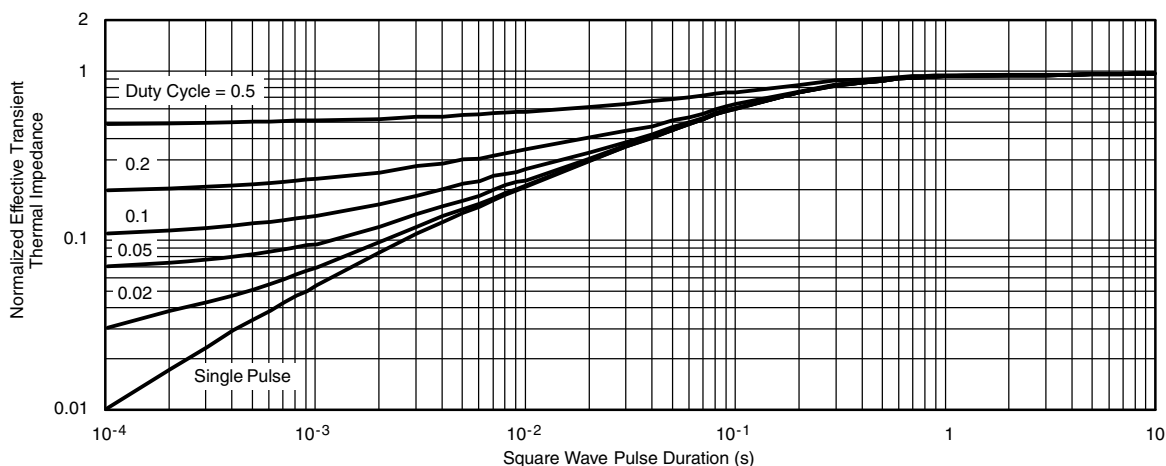
**Single Pulse Power (Junction-to-Ambient)**



**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



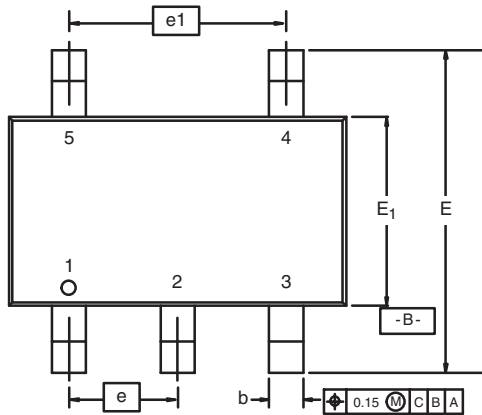
**Normalized Thermal Transient Impedance, Junction-to-Foot**

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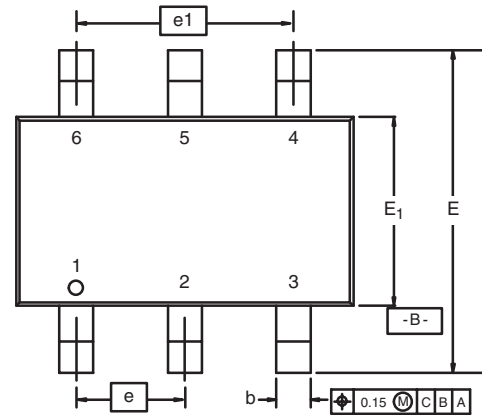


## TSOP: 5/6-LEAD

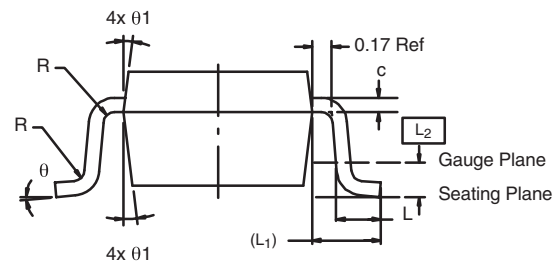
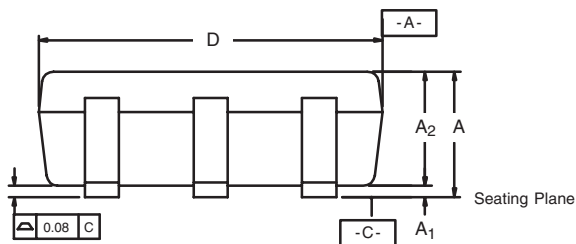
JEDEC Part Number: MO-193C



5-LEAD TSOP

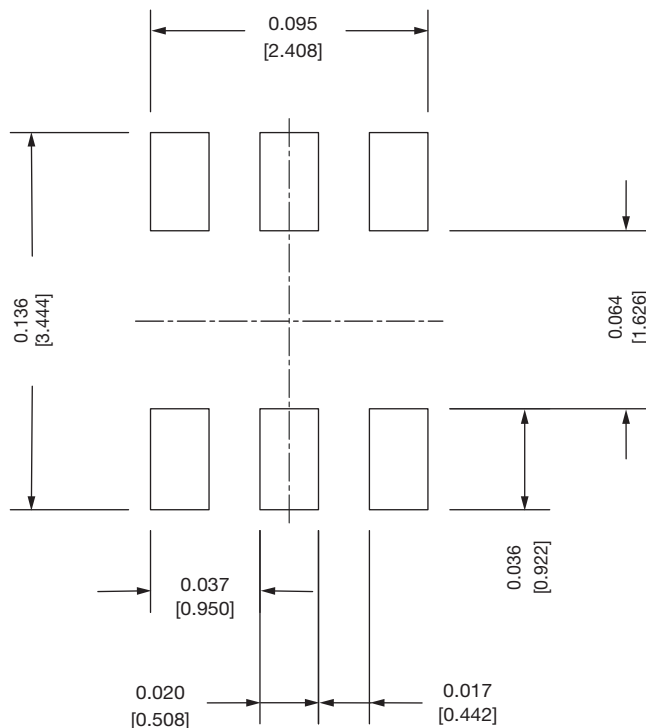
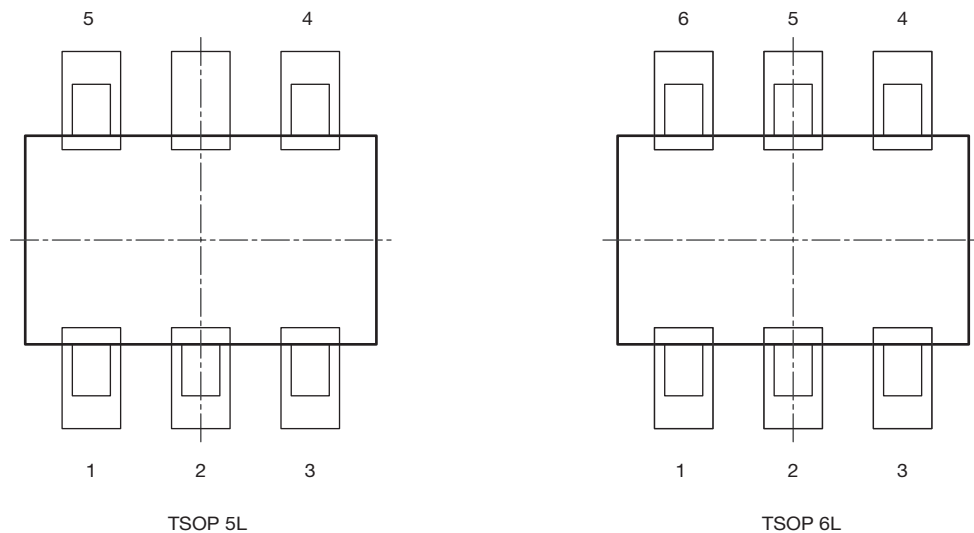


6-LEAD TSOP



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

## Recommended Land Pattern For TSOP-5L / TSOP-6L


**Note**

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022  
DWG: 3010



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